TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

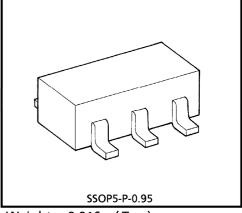
TC4S11F

2 INPUT NAND GATE

The TC4S11F is 2-input positive logic NAND gates. Gate output with inverter buffer improve the input-output characteristics and even if the load capacitance increases, it can be stopped the change of propagation time.

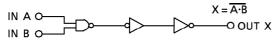
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	V_{DD}	$V_{SS} - 0.5 \sim V_{SS} + 20$	V
Input Voltage	V _{IN}	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	٧
Output Voltage	Vout	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	V
DC Input Current	IIN	± 10	mA
Power Dissipation	PD	200	mW
Operating Temperature Range	T _{opr}	- 40∼85	°C
Storage Temperature Range	T _{stg}	- 65~150	°C
Lead Temperature (10s)	TL	260	°C

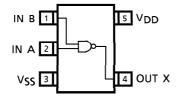


Weight: 0.016g (Typ.)

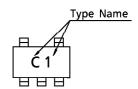
LOGIC DIAGRAM



PIN CONFIGURATION (TOP VIEW)



MARKING



1 2001-05-31

RECOMMENDED OPERATING CONDITIONS $(V_{SS} = 0V)$

CHARACTERISTIC	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V_{DD}	_	3	_	18	V
Input Voltage	VIN		0	_	V_{DD}	V

STATIC ELECTRICAL CHARACTERISTICS ($V_{SS} = 0V$)

CHARACTERISTIC		SYM- BOL	TEST CONDITION	V _{DD} (V)	– 40°C		25°C			85°C		UNIT
			TEST CONDITION		MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	OINIT
High-Level Output Voltage				5	4.95	_	4.95	5.00	_	4.95	_	
		VOH	I _{OUT} <1μΑ V _{IN} = V _{SS} , V _{DD}	10	9.95	_	9.95	10.00	_	9.95	_	
			VIN = VSS, VDD	15	14.95	-	14.95	15.00		14.95	-	v
Low-Level			l _{OUT} <1μΑ	5	_	0.05	_	0.00	l	_	0.05	, , ,
Output Vo		VOL	$V_{IN} = V_{DD}$	10	—	0.05	—	0.00	0.05	—	0.05	
Output V	Jitage		VIN	15	_	0.05	_	0.00	0.05	_	0.05	
			V _{OH} = 4.6V	5	- 0.61		- 0.51	- 1.0	_	- 0.42	_	
Output Hi	iah		V _{OH} = 2.5V	5	- 2.5	_	- 2.1	- 4.0	_	– 1.7	—	
Current	igii	ІОН	V _{OH} = 9.5V	10	– 1.5	_	- 1.3		1	- 1.1	_	
Current			V _{OH} = 13.5V	15	- 4.0	_	- 3.4	- 9.0	_	– 2.8	_	
			$V_{IN} = V_{SS}, V_{DD}$									0
			V _{OL} = 0.4V	5	0.61	_	0.51	1.2	_	0.42	_	mA
Output Lo	w		$V_{OL} = 0.5V$	10	1.5	_	1.3	3.2	_	1.1	_	
Current		lOL	V _{OL} = 1.5V	15	4.0	_	3.4	12.0	_	2.8	_	
			$V_{IN} = V_{DD}$									
		,,	V _{OUT} = 0.5V, 4.5V	5	3.5	_	3.5	2.75	_	3.5	_	
المائلة المستعددا	h \/_ 4		V _{OUT} = 1.0V, 9.0V	10	7.0	_	7.0	5.5	_	7.0	_	
Input Higl	n voitage	VIH	V _{OUT} = 1.5V, 13.5V	15	11.0	_	11.0	8.25	_	11.0	_	
			l _{OUT} <1μΑ	1								.,
			V _{OUT} = 4.5V	5	_	1.5	_	2.25	1.5	_	1.5	V
Input Low Voltage	VIL	V _{OUT} = 9.0V	10	l —	3.0	_	4.5	3.0	l —	3.0		
		V _{OUT} = 13.5V	15	l —	4.0	_	6.75	4.0	l —	4.0		
		l _{OUT} <1μΑ	1									
Input	H Level	ΊΗ	V _{IH} = 18V	18	_	0.1	_	10-5	0.1	_	1.0	^
Current	L Level	Ίμ	V _{IL} = 0V	18	_	- 0.1	_	– 10 ^{– 5}	-0.1	_	- 1.0	μ A
Quiescent Device Current			$V_{IN} = V_{SS}, V_{DD}$	5	_	0.25	_	0.001	0.25	_	7.5	
		I _{DD}	* NIM = ASS' ADD	10	—	0.5		0.001	0.5	—	15	μ A
			^	15		1.0		0.002	1.0		30	

^{*} All valid input combinations.

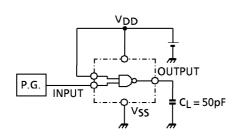
2 2001-05-31

DYNAMIC ELECTRICAL CHARACTERISTICS (Ta = 25°C, V_{SS} = 0V, C_L = 50pF)

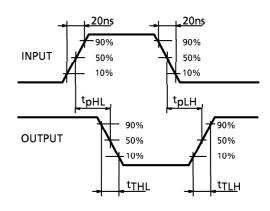
CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{DD} (V)	MIN.	TYP.	MAX.	UNIT
Output Transition Time			5	_	70	200	
(Low to High)	tTLH	-	10	_	35	100	
(LOW to High)			15	_	30	80	ns
Output Transition Time			5	_	70	200	
Output Transition Time	tTHL	_	10	_	35	100	
(High to Low)			15	_	30	80	
			5	_	65	200	
Propagation Delay Time	t _{pLH}	<u> </u>	10	_	30	100	
			15	_	25	80	
			5	_	65	200	ns
Propagation Delay Time	t _{pHL}	_	10	_	30	100	
			15	_	25	80	
Input Capacitance	CIN	_		_	5	7.5	pF

CIRCUIT AND WAVEFORM FOR MEASUREMENT OF DYNAMIC CHARACTERISTICS

TEST CIRCUIT



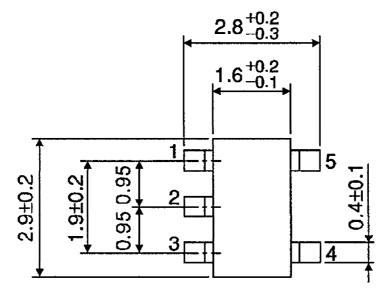
WAVEFORM

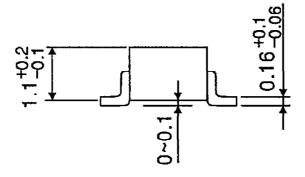


PACKAGE DIMENSIONS

SSOP5-P-0.95

Unit: mm





Weight: 0.016g (Typ.)

4 2001-05-31

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000707EBA

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